NTE ELECTRONICS, INC.
44 FARRAND STREET
BLOOMFIELD, NJ 07003
(973) 748–5089

NTE588
Silicon Diode
200V, 3A, Ultra Fast Switch

Features:

- High Reliability
- Low Leakage
- Low Forward Voltage
- High Current Capbility
- Super Fast Switching Speed < 35nS
- High Surge Capability
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- Good for 200kHz Power Supplier

Maximum Ratings and Electrical Characteristics: (T_A = +25°C unless otherwise specified. Single phase, half wave, 60Hz, resistive or inductive load. For capacitive load, derate current by 20%.)

Maximum Recurrent Peak Reverse Voltage	150V
Maximum RMS Voltage	105V
Maximum DC Blocking Voltage	150V
Maximum Average Forward Current (.375” (9.5mm) lead length at T_A = +55°C)	3A
Peak Forward Surge Current, I_{FM}surge 8.3ms single half sine–wave superimposed on rated load	125A
Maximum Forward Voltage at 3.0A DC	0.95V
Maximum DC Reverse Current at Rated DC Blocking Voltage	5µA
Maximum DC Reverse Current at Rated DC Blocking Voltage, T_A = 150°C	50µA
Maximum Reverse Recovery Time (Note 1)	35ns
Typical Junction Capacitance (Note 2)	155pF
Operating and Storage Temperature Range, T_J, T_{stg}	–65° to +150°C

Note 1. Reverse Recovery Test Conditions: $I_F = 0.5A$, $I_R = 1.0A$, $I_{RR} = 0.25A$
Note 2. Measured at 1MHz and applied reverse voltage of 4.0 volts.